

IN THE CLAIMS

Please cancel claims 1-10 without prejudice as being drawn to a non-elected invention.

Please amend claim 11.

Please add new claims 16-25.

Please enter the pending claims as follows:

1. – 10. (Canceled)

11. (Currently Amended) A structure comprising:

an anisotropic conductive film, said anisotropic conductive film comprising a front surface and a rear surface, said anisotropic conductive film comprising particles of a consistent shape;

a first raised contact disposed over said front surface, said first raised contact forming part of a first wafer; and

a second raised contact disposed over said rear surface, said second raised contact forming part of a second wafer, wherein said second raised contact faces said first raised contact.

12. (Original) The structure of claim 11 wherein said anisotropic conductive film comprises certain particles that are trapped between said first raised contact and said second raised contact.

13. (Original) The structure of claim 12 wherein said particles that are trapped between said first raised contact and said second raised contact form a continuous and conductive path.

14. (Original) The structure of claim 12 wherein said anisotropic conductive film further comprises other particles that are not trapped between said first raised contact and said second raised contact.

15. (Original) The structure of claim 13 wherein said particles that are not trapped between said first raised contact and said second raised contact do not form a continuous and conductive path.

16. (New) A stacked-substrate structure comprising:

a first substrate with a first surface, said first surface having a first raised contact;

an anisotropic conductive adhesive disposed over said first surface, said anisotropic conductive adhesive having particles with a consistent shape; and

a second substrate with a second surface, said second surface having a second raised contact, said second surface disposed over said anisotropic conductive adhesive, wherein said second raised contact faces said first raised contact, wherein some of said particles are trapped between said second raised contact and said first raised contact to form a continuous and conductive path.

17. (New) The stacked-substrate structure of claim 16 wherein said first surface is a front surface and said second surface is a front surface.

18. (New) The stacked-substrate structure of claim 16 wherein said first surface is a front surface and said second surface is a rear surface.

19. (New) The stacked-substrate structure of claim 16 wherein said first surface is a rear surface and said second surface is a rear surface.

20. (New) The stacked-substrate structure of claim 16 wherein said first substrate and said second substrate are structurally similar.

21. (New) The stacked-substrate structure of claim 16 wherein said first substrate and said second substrate are functionally similar.

22. (New) The stacked-substrate structure of claim 16 wherein said first substrate and said second substrate are structurally and functionally dissimilar.

23. (New) The stacked-substrate structure of claim 16 wherein said first substrate and said second substrate are pre-thinned.

24. (New) The stacked-substrate structure of claim 16 wherein said first substrate and said second substrate are wafers.

25. (New) The stacked-substrate structure of claim 16 wherein said first substrate and said second substrate are portions of wafers.